

LM148JAN

Quad 741 Op Amps

General Description

The LM148 is a true quad LM741. It consists of four independent, high gain, internally compensated, low power operational amplifiers which have been designed to provide functional characteristics identical to those of the familiar LM741 operational amplifier. In addition the total supply current for all four amplifiers is comparable to the supply current of a single LM741 type op amp. Other features include input offset currents and input bias current which are much less than those of a standard LM741. Also, excellent isolation between amplifiers has been achieved by independently biasing each amplifier and using layout techniques which minimize thermal coupling.

The LM148 can be used anywhere multiple LM741 or LM1558 type amplifiers are being used and in applications where amplifier matching or high packing density is required.

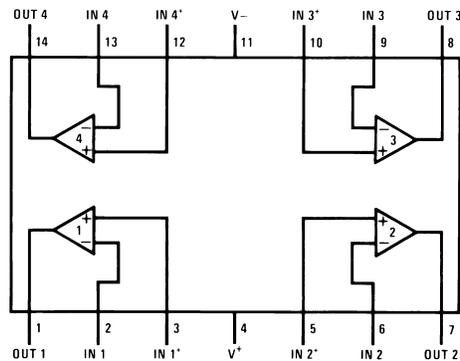
Features

- 741 op amp operating characteristics
- Class AB output stage—no crossover distortion
- Pin compatible with the LM124
- Overload protection for inputs and outputs
- Low supply current drain: 0.6 mA/Amplifier
- Low input offset voltage: 1 mV
- Low input offset current: 4 nA
- Low input bias current: 30 nA
- High degree of isolation between amplifiers: 120 dB
- Gain bandwidth product (unity gain): 1.0 MHz

Ordering Information

NS PART NUMBER	SMD PART NUMBER	NS PACKAGE NUMBER	PACKAGE DESCRIPTION
JL148BCA	JM38510/11001BCA	J14A	14LD CERDIP
JL148BDA	JM38510/11001BDA	W14B	14LD CERPACK
JL148BZA	JM38510/11001BZA	WG14A	14LD Ceramic SOIC
JL148SCA	JM38510/11001SCA	J14A	14LD CERDIP
JL148SDA	JM38510/11001SDA	W14B	14LD CERPACK

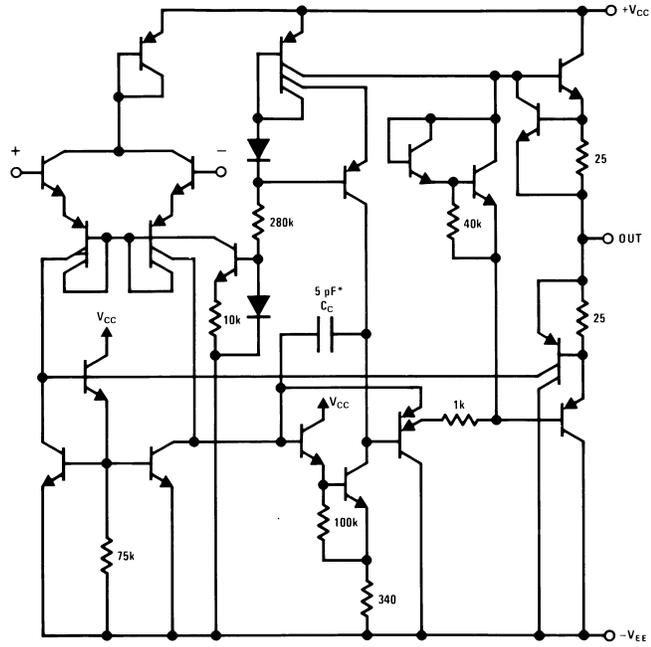
Connection Diagram



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Top View
See NS Package Number J14A, W14B, WG14A

Schematic Diagram



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* 1 pF in the LM149

Absolute Maximum Ratings (Note 1)

Supply Voltage	±22V
Input Voltage Range	±20V
Input Current Range	-0.1mA to 10mA
Differential Input Voltage (Note 2)	±30V
Output Short Circuit Duration (Note 3)	Continuous
Power Dissipation (P_d at 25°C) (Note 4)	
CERDIP	400mW
CERPACK	350mW
Thermal Resistance	
θ_{JA}	
CERDIP (Still Air)	103°C/W
CERDIP (500LF/ Min Air flow)	52°C/W
CERPACK (Still Air)	140°C/W
CERPACK (500LF/ Min Air flow)	100°C/W
Ceramic SOIC (Still Air)	176°C/W
Ceramic SOIC (500LF/ Min Air flow)	116°C/W
θ_{JC}	
CERDIP	19°C/W
CERPACK	25°C/W
Ceramic SOIC	25°C/W
Package Weight (typical)	
CERDIP	TBD
CERPACK	465mg
Ceramic SOIC	415mg
Maximum Junction Temperature (T_{JMAX})	175°C
Operating Temperature Range	-55°C ≤ T_A ≤ +125°C
Storage Temperature Range	-65°C ≤ T_A ≤ +150°C
Lead Temperature (Soldering, 10 sec.) Ceramic	300°C
ESD tolerance (Note 5)	500V

Quality Conformance Inspection

MIL-STD-883, Method 5005 — Group A

Subgroup	Description	Temp (°C)
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

Electrical Characteristics

DC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $\pm V_{CC} = \pm 20V$, $V_{CM} = 0V$, measure each amplifier.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
V_{IO}	Input Offset Voltage	$+V_{CC} = 35V, -V_{CC} = -5V,$ $V_{CM} = -15V$		-5.0	+5.0	mV	1
				-6.0	+6.0	mV	2, 3
		$+V_{CC} = 5V, -V_{CC} = -35V,$ $V_{CM} = +15V$		-5.0	+5.0	mV	1
				-6.0	+6.0	mV	2, 3
		$+V_{CC} = 5V, -V_{CC} = -5V,$		-5.0	+5.0	mV	1
				-6.0	+6.0	mV	2, 3
Delta V_{IO} / Delta T	Input Offset Voltage Temperature Stability	$25^{\circ}C \leq T_A \leq 125^{\circ}C$	(Note 6)	-25	25	$\mu V/^{\circ}C$	2
		$-55^{\circ}C \leq T_A \leq 25^{\circ}C$	(Note 6)	-25	25	$\mu V/^{\circ}C$	3
I_{IO}	Input Offset Current	$+V_{CC} = 35V, -V_{CC} = -5V,$ $V_{CM} = -15V$		-25	+25	nA	1, 2
				-75	+75	nA	3
		$+V_{CC} = 5V, -V_{CC} = -35V,$ $V_{CM} = +15V$		-25	+25	nA	1, 2
				-75	+75	nA	3
		$+V_{CC} = 5V, -V_{CC} = -5V,$		-25	+25	nA	1, 2
				-75	+75	nA	3
Delta I_{IO} / Delta T	Input Offset Current Temperature Stability	$25^{\circ}C \leq T_A \leq 125^{\circ}C$	(Note 6)	-200	200	$pA/^{\circ}C$	2
		$-55^{\circ}C \leq T_A \leq 25^{\circ}C$	(Note 6)	-400	400	$pA/^{\circ}C$	3
$\pm I_{IB}$	Input Bias Current	$+V_{CC} = 35V, -V_{CC} = -5V,$ $V_{CM} = -15V$		-0.1	100	nA	1, 2
				-0.1	325	nA	3
		$+V_{CC} = 5V, -V_{CC} = -35V,$ $V_{CM} = +15V$		-0.1	100	nA	1, 2
				-0.1	325	nA	3
		$+V_{CC} = 5V, -V_{CC} = -5V,$		-0.1	100	nA	1, 2
				-0.1	325	nA	3
PSRR+	Power Supply Rejection Ratio	$-V_{CC} = -20V, +V_{CC} = 20V$ to 10V	(Note 7)	-100	100	$\mu V/V$	1, 2, 3
PSRR-	Power Supply Rejection Ratio	$+V_{CC} = 20V, -V_{CC} = -20V$ to -10V	(Note 7)	-100	100	$\mu V/V$	1, 2, 3
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 15V, \pm 5V \leq V_{CC} \leq \pm 35V$		76		dB	1, 2, 3

Electrical Characteristics

AC / DC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.)
 $\pm V_{CC} = \pm 20V$, $V_{CM} = 0V$, measure each amplifier.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
$+ I_{OS}$	Short Circuit Current	$+V_{CC} = 15V, -V_{CC} = -15V,$ $V_{CM} = -10V$		-55		mA	1, 2
				-75		mA	3
$- I_{OS}$	Short Circuit Current	$+V_{CC} = 15V, -V_{CC} = -15V,$ $V_{CM} = +10V$			55	mA	1, 2
					75	mA	3
I_{CC}	Power Supply Current	$+V_{CC} = 15V, -V_{CC} = -15V$			3.6	mA	1
					4.5	mA	2, 3
$-A_{VS}$	Open Loop Voltage Gain	$V_{OUT} = -15V, R_L = 10K\Omega$		50		V/mV	4
				25		V/mV	5, 6
		$V_{OUT} = -15V, R_L = 2K\Omega$		50		V/mV	4
				25		V/mV	5, 6

Electrical Characteristics (Continued)

AC / DC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.)

$\pm V_{CC} = \pm 20V$, $V_{CM} = 0V$, measure each amplifier.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
$+A_{VS}$	Open Loop Voltage Gain	$V_{OUT} = +15V$, $R_L = 10K\Omega$		50		V/mV	4
				25		V/mV	5, 6
		$V_{OUT} = +15V$, $R_L = 2K\Omega$		50		V/mV	4
				25		V/mV	5, 6
A_{VS}	Open Loop Voltage Gain	$V_{CC} = \pm 5V$, $V_{OUT} = \pm 2V$, $R_L = 10K\Omega$		10		V/mV	4, 5, 6
		$V_{CC} = \pm 5V$, $V_{OUT} = \pm 2V$, $R_L = 2K\Omega$		10		V/mV	4, 5, 6
$+V_{OP}$	Output Voltage Swing	$R_L = 10K\Omega$		+16		V	4, 5, 6
		$R_L = 2K\Omega$		+15		V	4, 5, 6
$-V_{OP}$	Output Voltage Swing	$R_L = 10K\Omega$			-16	V	4, 5, 6
		$R_L = 2K\Omega$			-15	V	4, 5, 6
TR_{TR}	Transient Response Time	$V_{IN} = 50mV$, $A_V = 1$			1	μS	7, 8A, 8B
TR_{OS}	Transient Response Time	$V_{IN} = 50mV$, $A_V = 1$			25	%	7, 8A, 8B
$\pm SR$	Slew Rate	$V_{IN} = -5V$ to $+5V$, $A_V = 1$		0.2		V/ μS	7, 8A, 8B
		$V_{IN} = +5V$ to $-5V$, $A_V = 1$		0.2		V/ μS	7, 8A, 8B

Electrical Characteristics

AC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $\pm V_{CC} = \pm 20V$, $V_{CM} = 0V$, measure each amplifier.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
NI_{BB}	Noise (Broadband)	$BW = 10Hz$ to $5KHz$			15	μV_{RMS}	7
NI_{PC}	Noise (Popcorn)	$R_S = 20K\Omega$			40	μV_{PK}	7
C_S	Channel Separation	$V_{IN} = \pm 10V$, A to B, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, A to C, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, A to D, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, B to A, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, B to C, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, B to D, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, C to A, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, C to B, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, C to D, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, D to A, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, D to B, $R_L = 2K\Omega$		80		dB	7
		$V_{IN} = \pm 10V$, D to C, $R_L = 2K\Omega$		80		dB	7

Electrical Characteristics

DC DRIFT PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $\pm V_{CC} = \pm 20V$, $V_{CM} = 0V$, measure each amplifier. Delta calculations performed on JAN S and QMLV devices at group B, subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
V_{IO}	Input Offset Voltage			-1	1	mV	1
$\pm I_{IB}$	Input Bias Current			-15	15	nA	1

Electrical Characteristics (Continued)

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 2: The differential input voltage range shall not exceed the supply voltage range.

Note 3: Any of the amplifier outputs can be shorted to ground indefinitely; however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

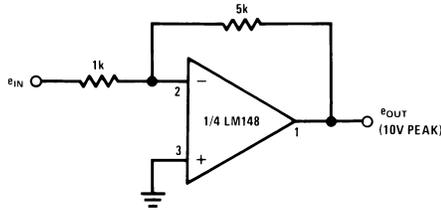
Note 4: The maximum power dissipation for these devices must be derated at elevated temperatures and is indicated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_d = (T_{JMAX} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is less.

Note 5: Human body model, 1.5 k Ω in series with 100 pF.

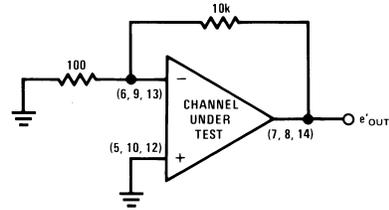
Note 6: Calculated parameter.

Note 7: Datalogs as μV

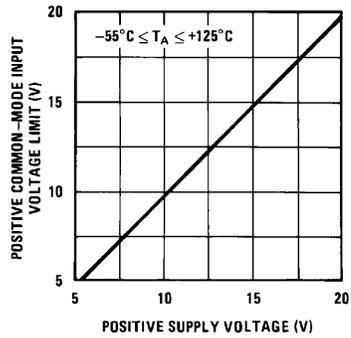
Cross Talk Test Circuit $V_S = \pm 15V$



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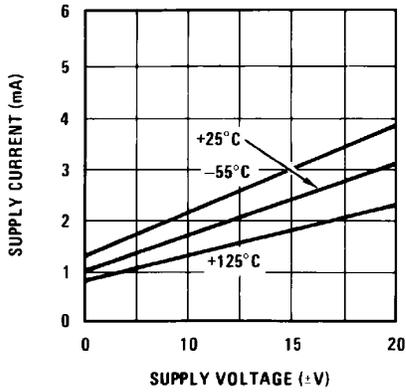
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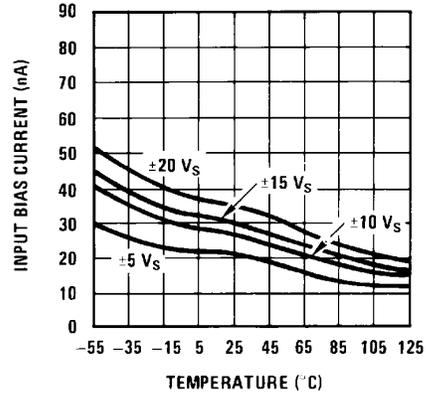
Typical Performance Characteristics

Supply Current



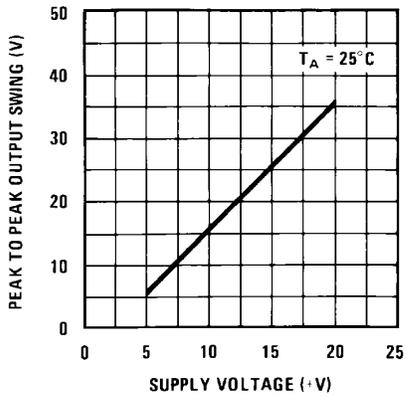
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Input Bias Current



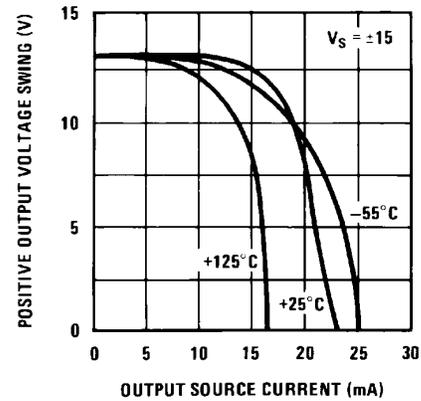
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Voltage Swing



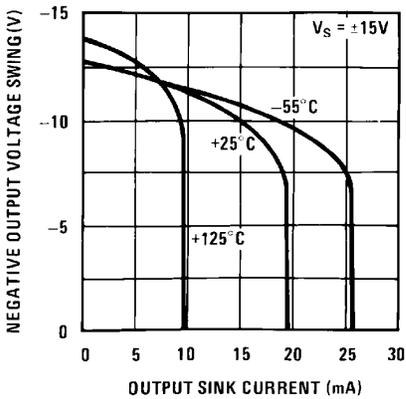
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Positive Current Limit



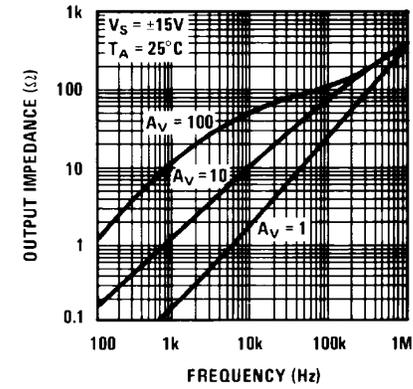
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Negative Current Limit



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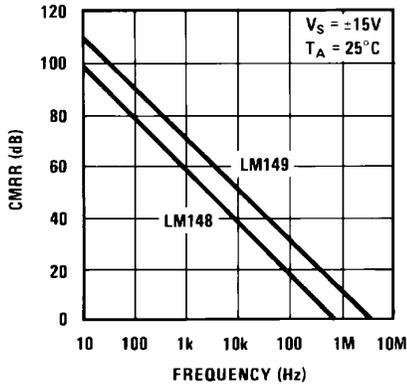
Output Impedance



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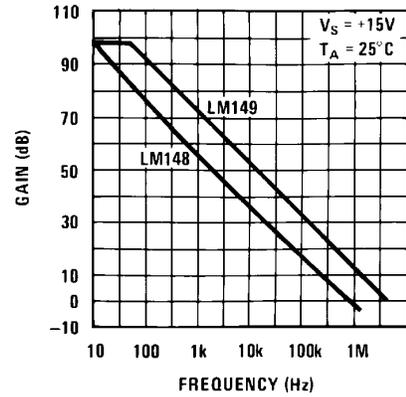
Typical Performance Characteristics (Continued)

Common-Mode Rejection Ratio



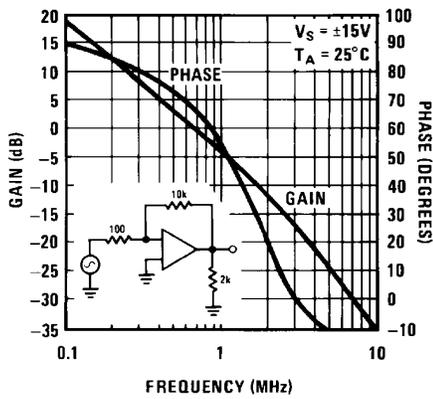
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Open Loop Frequency Response



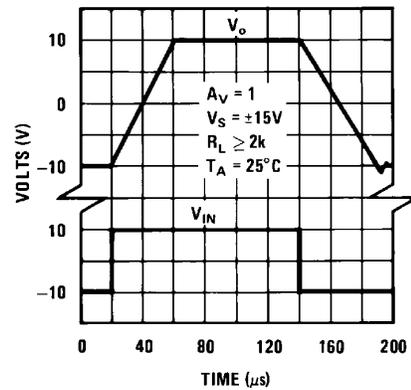
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Bode Plot LM148



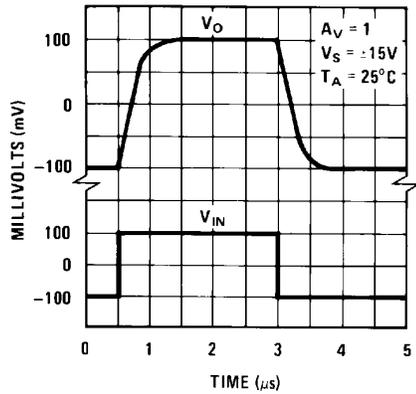
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Large Signal Pulse Response (LM148)



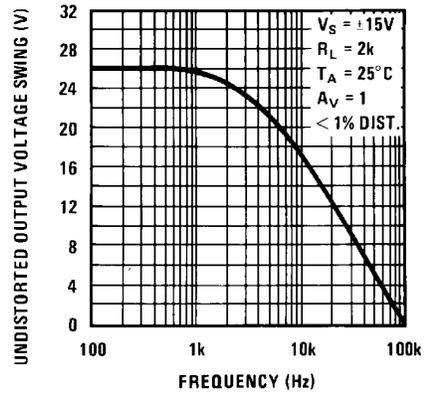
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Small Signal Pulse Response (LM148)



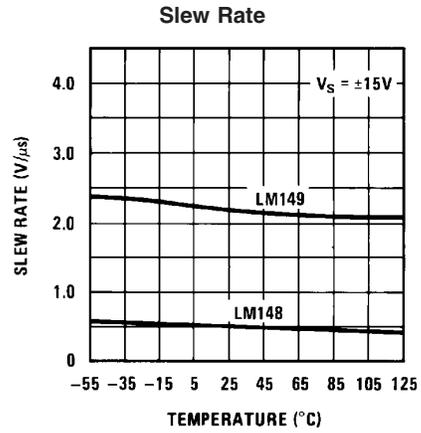
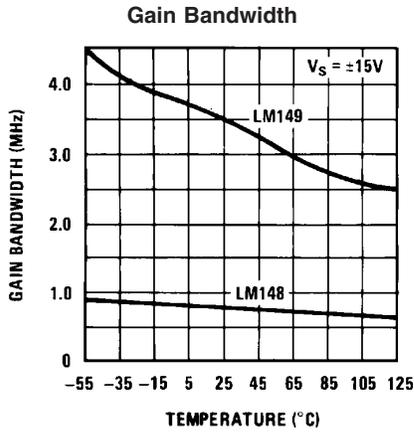
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Undistorted Output Voltage Swing

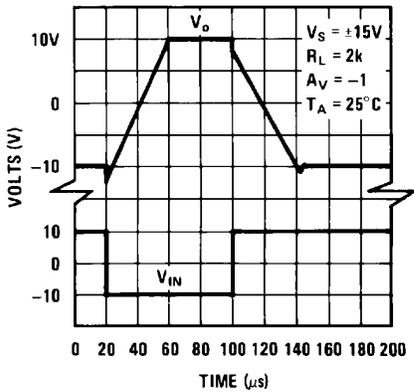


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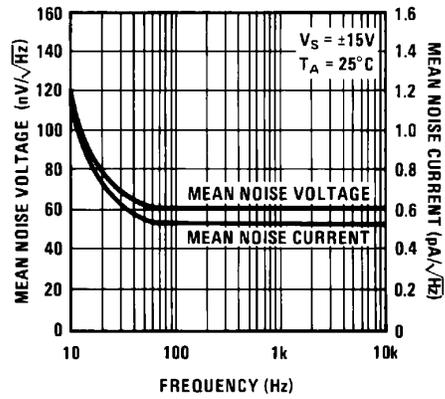
Typical Performance Characteristics (Continued)



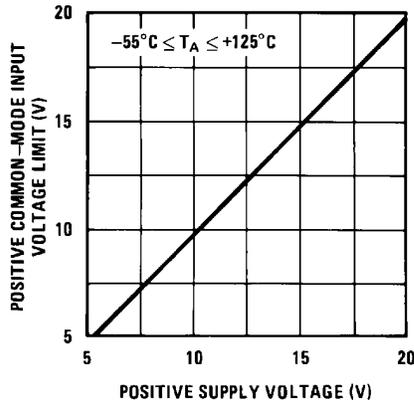
Inverting Large Signal Pulse Response (LM148)



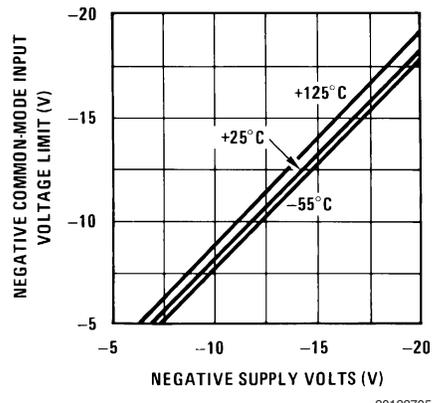
Input Noise Voltage and Noise Current



Positive Common-Mode Input Voltage Limit

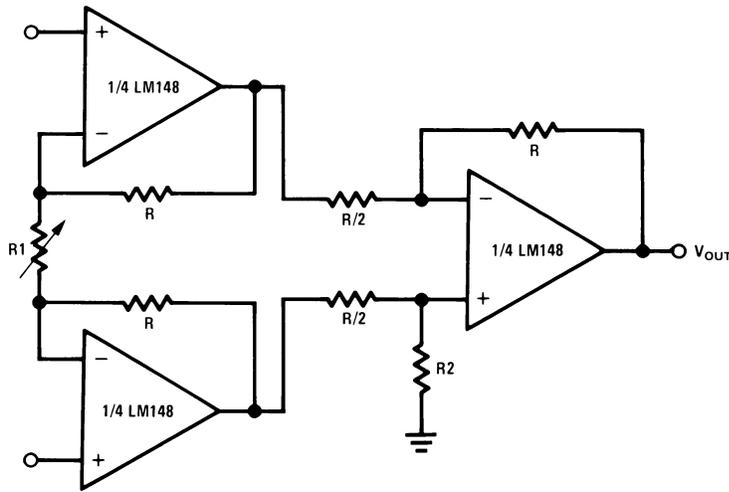


Negative Common-Mode Input Voltage Limit



Typical Applications—LM148 (Continued)

Low Cost Instrumentation Amplifier



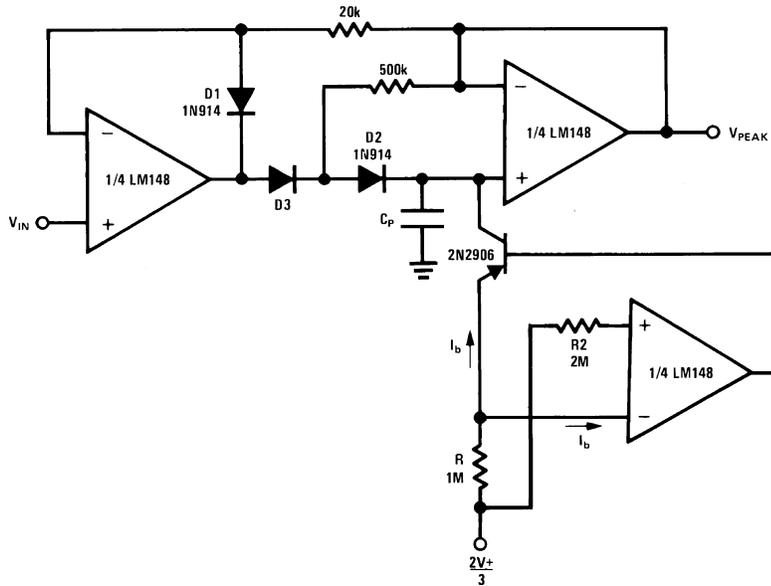
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$$V_{OUT} = 2 \left(\frac{2R}{R1} + 1 \right) \cdot V_S - 3V \leq V_{IN\ CM} \leq V_S^+ - 3V,$$

$V_S = \pm 15V$

$R = R2$, trim $R2$ to boost CMRR

Low Drift Peak Detector with Bias Current Compensation



20122710

Adjust R for minimum drift

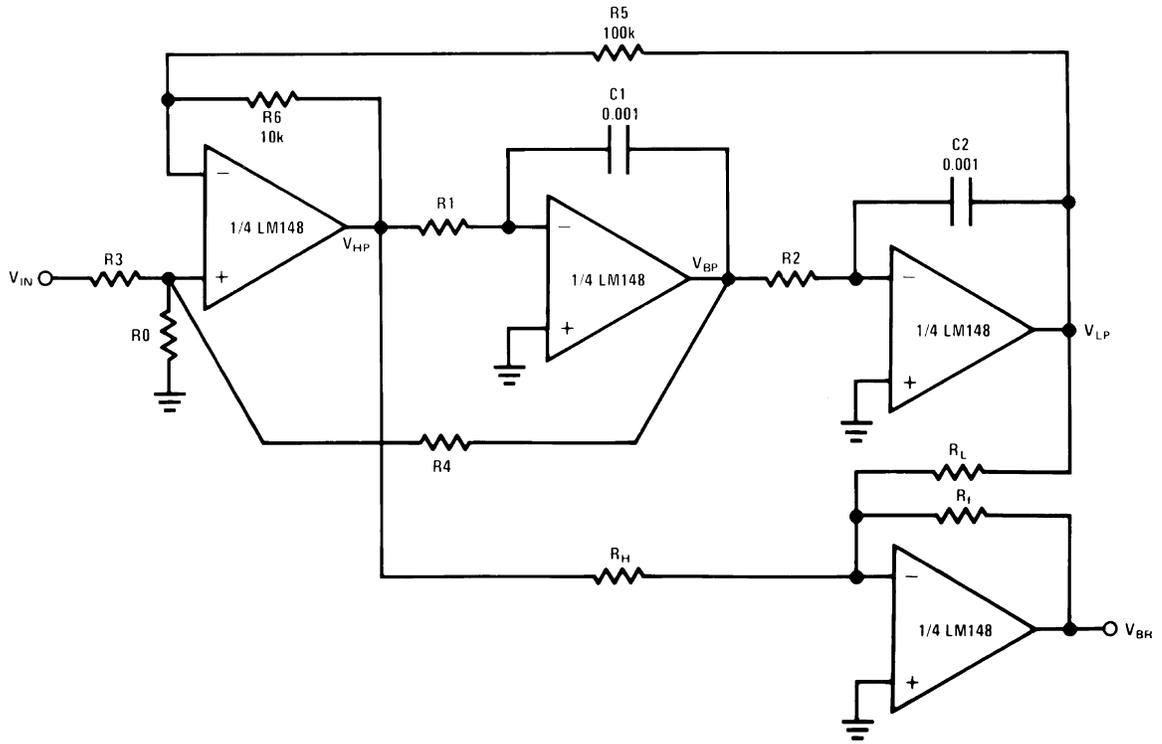
$D3$ low leakage diode

$D1$ added to improve speed

$V_S = \pm 15V$

Typical Applications—LM148 (Continued)

Universal State-Variable Filter



20122711

Tune Q through R0,
 For predictable results: $f_0 Q \leq 4 \times 10^4$
 Use Band Pass output to tune for Q

$$\frac{V(s)}{V_{IN}(s)} = \frac{N(s)}{D(s)}, D(s) = s^2 + \frac{s\omega_0}{Q} + \omega_0^2$$

$$N_{HP}(s) = s^2 H_{OHP}, N_{BP}(s) = \frac{-s\omega_0 H_{OBP}}{Q}, N_{LP} = \omega_0^2 H_{OLP}$$

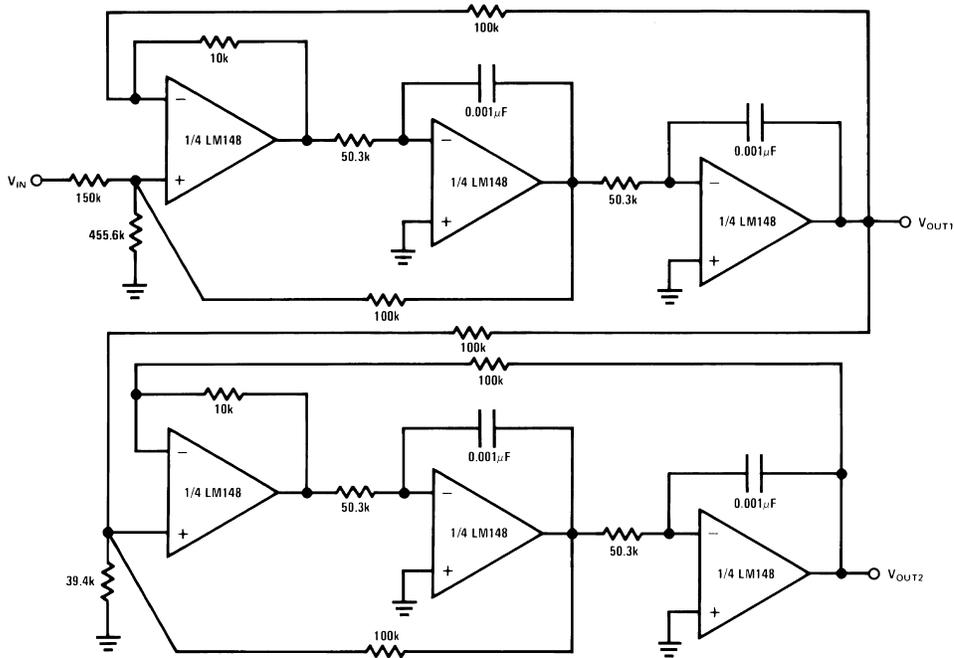
$$f_0 = \frac{1}{2\pi} \sqrt{\frac{R_6}{R_5}} \sqrt{\frac{1}{t_1 t_2}}, t_i = R_i C_i, Q = \left(\frac{1 + R_4/R_3 + R_4/R_0}{1 + R_6/R_5} \right) \left(\frac{R_6 t_1}{R_5 t_2} \right)^{1/2}$$

$$f_{NOTCH} = \frac{1}{2\pi} \left(\frac{R_H}{R_L t_1 t_2} \right)^{1/2}, H_{OHP} = \frac{1 + R_6/R_5}{1 + R_3/R_0 + R_3/R_4}, H_{OBP} = \frac{1 + R_4/R_3 + R_4/R_0}{1 + R_3/R_0 + R_3/R_4}$$

$$H_{OLP} = \frac{1 + R_5/R_6}{1 + R_3/R_0 + R_3/R_4}$$

Typical Applications—LM148 (Continued)

A 1 kHz 4 Pole Butterworth



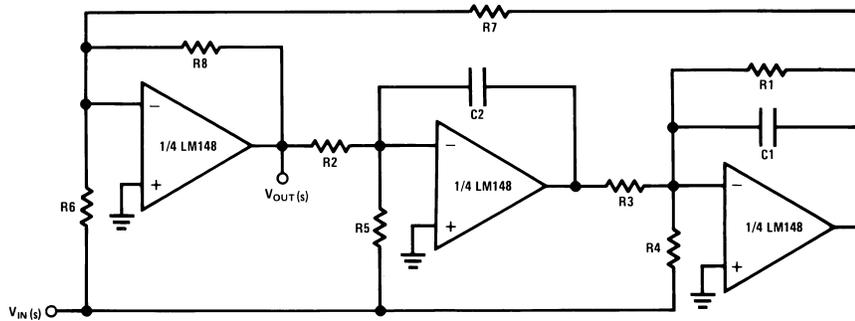
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Use general equations, and tune each section separately

$Q_{1stSECTION} = 0.541$, $Q_{2ndSECTION} = 1.306$

The response should have 0 dB peaking

A 3 Amplifier Bi-Quad Notch Filter



20122713

$$Q = \sqrt{\frac{R8}{R7}} \times \frac{R1C1}{\sqrt{R3C2R2C1}}, f_o = \frac{1}{2\pi} \sqrt{\frac{R8}{R7}} \times \frac{1}{\sqrt{R2R3C1C2}}, f_{NOTCH} = \frac{1}{2\pi} \sqrt{\frac{R6}{R3R5R7C1C2}}$$

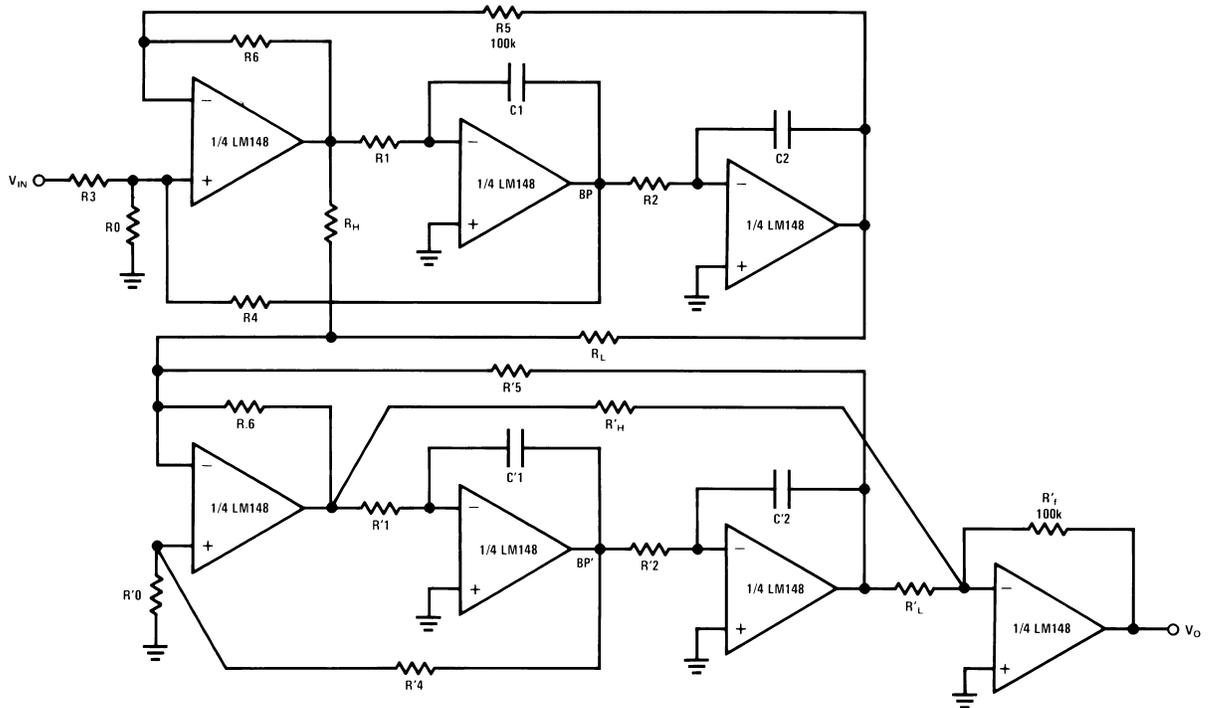
$$\text{Necessary condition for notch: } \frac{1}{R6} = \frac{R1}{R4R7}$$

Ex: $f_{NOTCH} = 3$ kHz, $Q = 5$, $R1 = 270k$, $R2 = R3 = 20k$, $R4 = 27k$, $R5 = 20k$, $R6 = R8 = 10k$, $R7 = 100k$, $C1 = C2 = 0.001 \mu F$

Better noise performance than the state-space approach.

Typical Applications—LM148 (Continued)

A 4th Order 1 kHz Elliptic Filter (4 Poles, 4 Zeros)



20122714

$$R1C1 = R2C2 = t$$

$$R'1C'1 = R'2C'2 = t'$$

$f_C = 1 \text{ kHz}$, $f_S = 2 \text{ kHz}$, $f_p = 0.543$, $f_z = 2.14$, $Q = 0.841$, $f'_p = 0.987$, $f'_z = 4.92$, $Q' = 4.403$, normalized to ripple BW

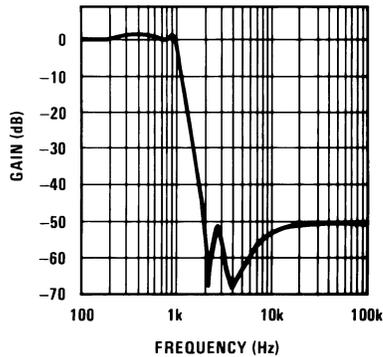
$$f = \frac{1}{2\pi R1C1} \times \sqrt{K}, K = \frac{R4R5}{R3} \left(\frac{1}{r_{DS}} + \frac{1}{R4} + \frac{1}{R5} \right), r_{DS} \approx \frac{R_{ON}}{\left(1 - \frac{V_{GS}}{V_P}\right)^{1/2}}$$

Use the BP outputs to tune Q, Q', tune the 2 sections separately

$R1 = R2 = 92.6k$, $R3 = R4 = R5 = 100k$, $R6 = 10k$, $R0 = 107.8k$, $R_L = 100k$, $R_H = 155.1k$,

$R'1 = R'2 = 50.9k$, $R'4 = R'5 = 100k$, $R'6 = 10k$, $R'0 = 5.78k$, $R'_L = 100k$, $R'_H = 248.12k$, $R'_f = 100k$. All capacitors are 0.001 μF .

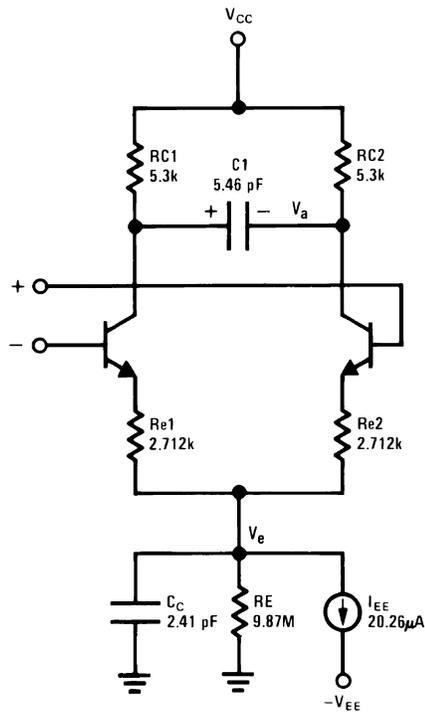
Lowpass Response



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Typical Simulation

LM148, LM741 Macromodel for Computer Simulation

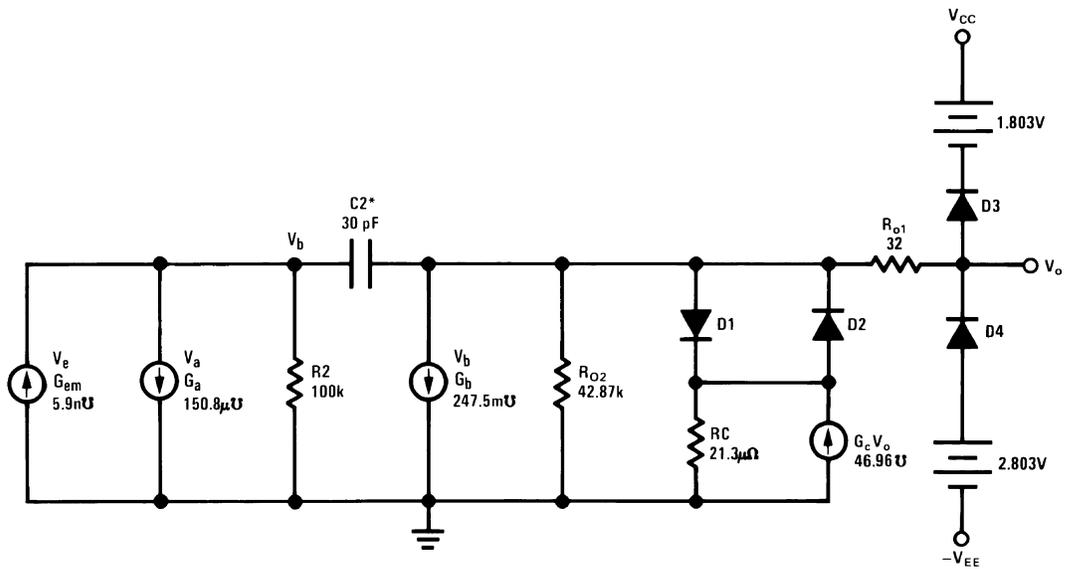


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For more details, see IEEE Journal of Solid-State Circuits, Vol. SC-9, No. 6, December 1974

Note 8: $\omega_1 = 112I_S = 8 \times 10^{-16}$

Note 9: $\omega_2 = 144^{\circ}C2 = 6 \text{ pF}$ for LM149



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Revision History Section

Date Released	Revision	Section	Originator	Changes
02/15/05	A	New Release, Corporate format	L. Lytle	1 MDS data sheet converted into one Corp. data sheet format. MJLM148-X, Rev. 0C1. MDS data sheet will be archived.

